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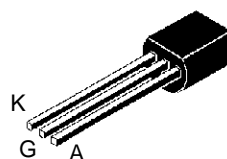
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SENSITIVE GATE SCR
FEATURES

- $I_{T(RMS)} = 1.25A$
- $V_{DRM} = 200V$ to $800V$
- Low $I_{GT} < 200 \mu A$

DESCRIPTION

The X02xxxA series of SCRs uses a high performance TOP GLASS PNP technology. These parts are intended for general purpose applications where low gate sensitivity is required.



TO92
(Plastic)

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	$T_I = 60^\circ C$ 1.25	A
$I_{T(AV)}$	Mean on-state current (180° conduction angle)	$T_I = 60^\circ C$ 0.8	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = $25^\circ C$)	$t_p = 8.3$ ms	25
		$t_p = 10$ ms	22.5
I_t^2	I_t^2 Value for fusing	$t_p = 10$ ms	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 10$ mA $di_G/dt = 0.1$ A/ μs .	30	A/ μs
T_{stg} T_j	Storage and operating junction temperature range	- 40, + 150 - 40, + 125	$^\circ C$
T_I	Maximum lead temperature for soldering during 10s at 2mm from case	260	$^\circ C$

Symbol	Parameter	Voltage				Unit
		B	D	M	N	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ C$ $R_{GK} = 1K\Omega$	200	400	600	800	V

X02xxxA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Junction to ambient	150	°C/W
Rth(j-l)	Junction to leads for DC	60	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)} = 0.2 \text{ W}$ $P_{GM} = 3 \text{ W}$ ($t_p = 20 \mu\text{s}$) $I_{GM} = 1.2 \text{ A}$ ($t_p = 20 \mu\text{s}$)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Sensitivity			Unit
				02	03	05	
I _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MIN		20	20	μA
			MAX	200	200	50	
V _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MAX	0.8			V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ R _{GK} = 1 KΩ	T _j = 125°C	MIN	0.1			V
V _{RGM}	I _{RG} = 10μA	T _j = 25°C	MIN	8			V
t _{gd}	V _D =V _{DRM} I _{TM} = 3 x I _{T(AV)} dI _G /dt = 0.1A/μs I _G = 10mA	T _j = 25°C	TYP	0.5			μs
I _H	I _T = 50mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	5			mA
I _L	I _G =1mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	6			mA
V _{TM}	I _{TM} = 2.5A t _p = 380μs	T _j = 25°C	MAX	1.45			V
I _{DRM} I _{RRM}	V _D = V _{DRM} R _{GK} = 1 KΩ V _R = V _{RRM}	T _j = 25°C	MAX	5			μA
		T _j = 110°C	MAX	200			μA
dV/dt	V _D =67%V _{DRM} R _{GK} = 1 KΩ	T _j = 110°C	TYP	15	20	15	V/μs
t _q	I _{TM} = 3 x I _{T(AV)} V _R =35V dI/dt=10A/μs t _p =100μs dV/dt=2V/μs V _D = 67%V _{DRM} R _{GK} = 1 KΩ	T _j = 110°C	MAX	100			μs

ORDERING INFORMATION

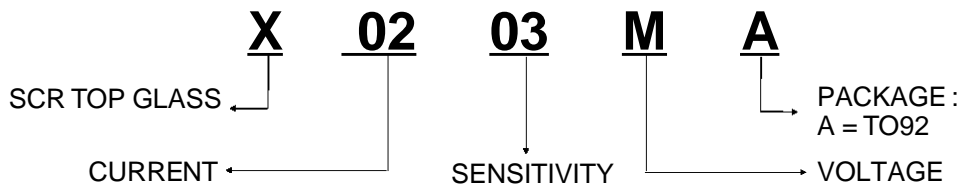


Fig.1 : Maximum average power dissipation versus average on-state current.

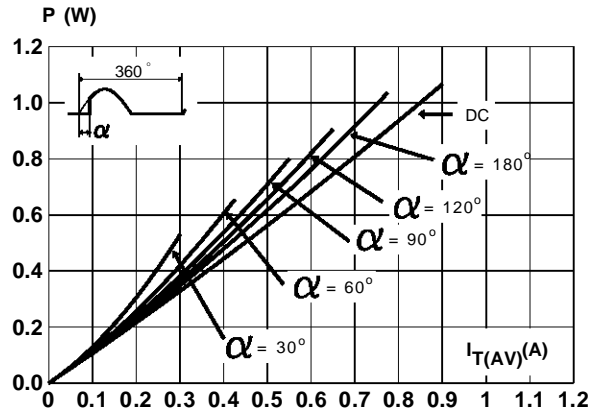


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tlead).

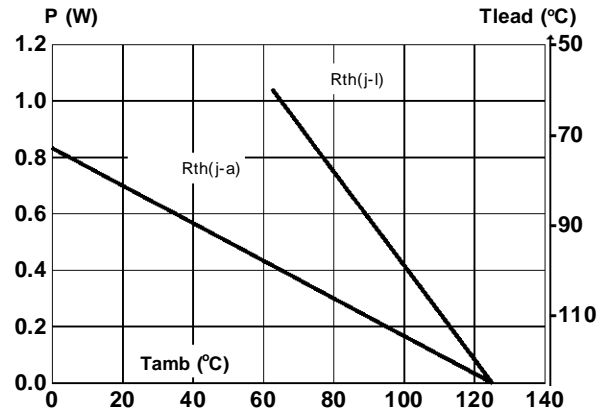


Fig.3 : Average on-state current versus lead temperature.

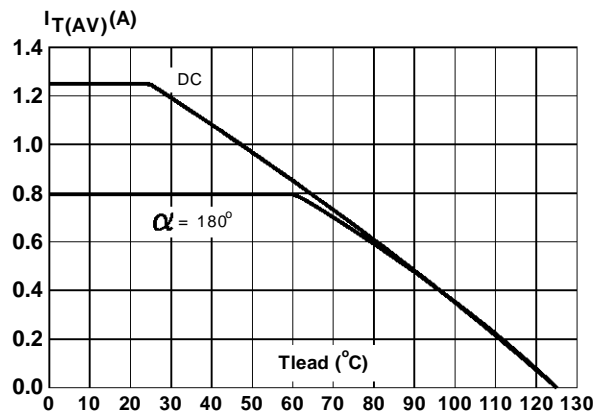


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

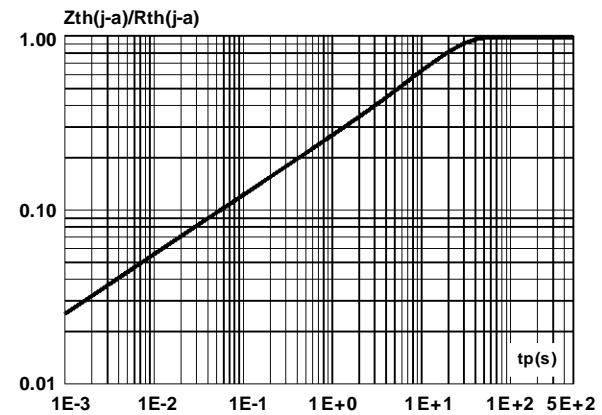


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

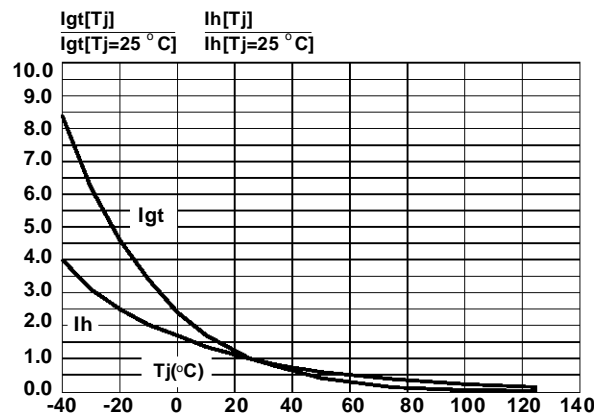
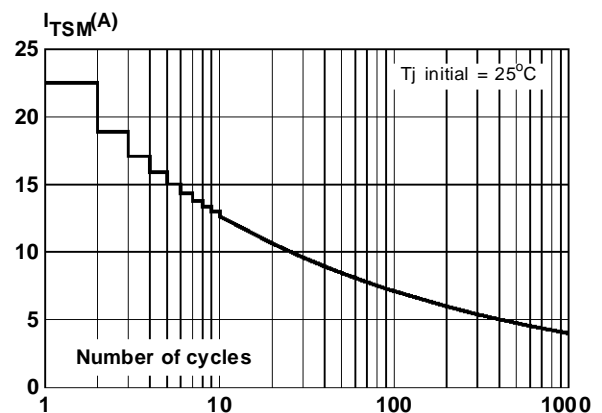


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



X02xxxA

Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

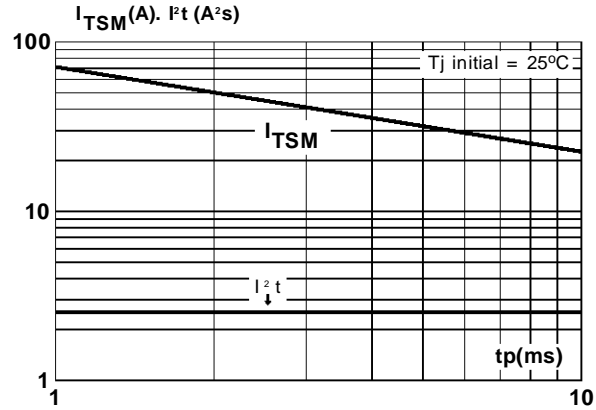
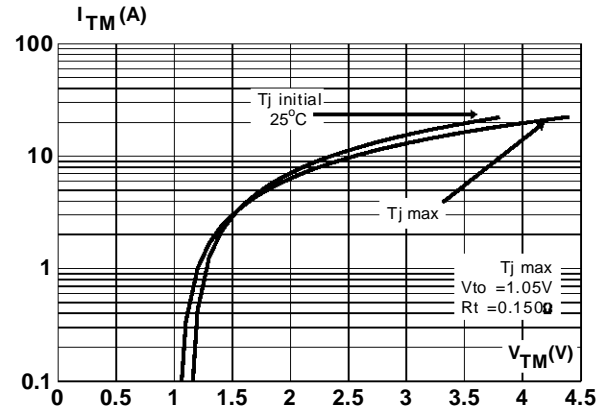


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO92 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Typ.	Min.	Max.	Typ.	Min.	Max.
A	1.35			0.053		
B			4.7			0.185
C	2.54			0.100		
D		4.4	4.8		0.173	0.189
E		12.7			0.500	
F			3.7			0.146
a			0.45			0.017

Marking : Type number

Weight : 0.2 g

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